

## D Series Power MOSFET



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HALOGEN  
**FREE**  
Available

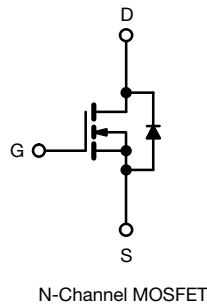
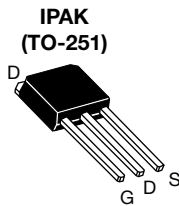
PRODUCT SUMMARY		
$V_{DS}$ (V) at $T_J$ max.	550	
$R_{DS(on)}$ max. ( $\Omega$ ) at 25 °C	$V_{GS} = 10$ V	1.5
$Q_g$ max. (nC)	20	
$Q_{gs}$ (nC)	3	
$Q_{gd}$ (nC)	5	
Configuration	Single	

### FEATURES

- Optimal design
  - Low area specific on-resistance
  - Low input capacitance ( $C_{iss}$ )
  - Reduced capacitive switching losses
  - High body diode ruggedness
  - Avalanche energy rated (UIS)
- Optimal efficiency and operation
  - Low cost
  - Simple gate drive circuitry
  - Low figure-of-merit (FOM):  $R_{on} \times Q_g$
  - Fast switching
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

### APPLICATIONS

- Consumer electronics
  - Displays (LCD or plasma TV)
- Server and telecom power supplies
  - SMPS
- Industrial
  - Welding
  - Induction heating
  - Motor drives
- Battery chargers




ORDERING INFORMATION	
Package	IPAK (TO-251)
Lead (Pb)-free	SiHU5N50D-E3
Lead (Pb)-free and Halogen-free	SiHU5N50D-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	500	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	
Gate-Source Voltage AC ( $f > 1$ Hz)		30	
Continuous Drain Current ( $T_J = 150$ °C)	$V_{GS}$ at 10 V	$T_C = 25$ °C	5.3
		$T_C = 100$ °C	3.4
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	10	A
Linear Derating Factor		0.83	W/°C
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	28.8	mJ
Maximum Power Dissipation	$P_D$	104	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C
Drain-Source Voltage Slope	$dV/dt$	$T_J = 125$ °C	24
Reverse Diode $dV/dt$ <sup>d</sup>		0.28	
Soldering Recommendations (Peak temperature) <sup>c</sup>	for 10 s	300	°C

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 2.3$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 5$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ , starting  $T_J = 25$  °C.

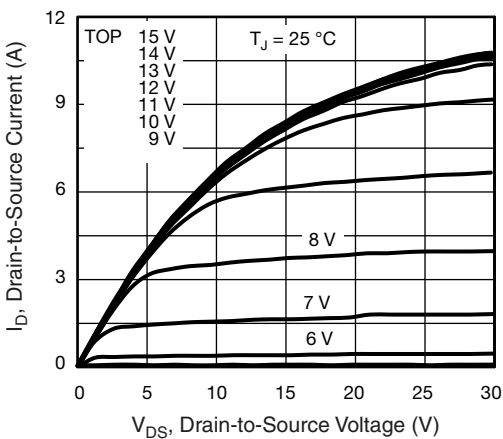
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	1.2	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	500	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 250\text{ }\mu\text{A}$	-	0.58	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3	-	5	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$	-	1.2	1.5	$\Omega$
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 20\text{ V}, I_D = 2.5\text{ A}$	-	1.8	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	325	-	pF
Output Capacitance	$C_{oss}$		-	34	-	
Reverse Transfer Capacitance	$C_{rss}$		-	6	-	
Effective Output Capacitance, Energy Related <sup>b</sup>	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	-	31	-	
Effective Output Capacitance, Time Related <sup>c</sup>	$C_{o(tr)}$		-	41	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}, V_{DS} = 400\text{ V}$	-	10	20	nC
Gate-Source Charge	$Q_{gs}$		-	3	-	
Gate-Drain Charge	$Q_{gd}$		-	5	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 2.5\text{ A}, R_g = 9.1\text{ }\Omega, V_{GS} = 10\text{ V}$	-	12	24	ns
Rise Time	$t_r$		-	11	22	
Turn-Off Delay Time	$t_{d(off)}$		-	14	28	
Fall Time	$t_f$		-	11	22	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}, \text{open drain}$	-	1.7	-	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse P - N junction diode 	-	-	5	A
Pulsed Diode Forward Current	$I_{SM}$		-	-	20	
Diode Forward Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 4\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 2.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 20\text{ V}$	-	320	-	ns
Reverse Recovery Charge	$Q_{rr}$		-	1.2	-	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$		-	8	-	A

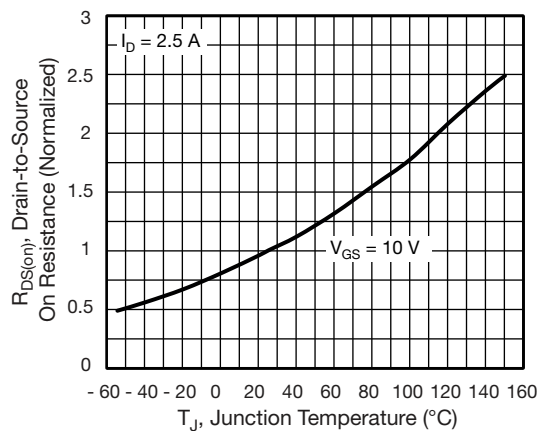
**Notes**

- Repetitive rating; pulse width limited by maximum junction temperature.
- $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .
- $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

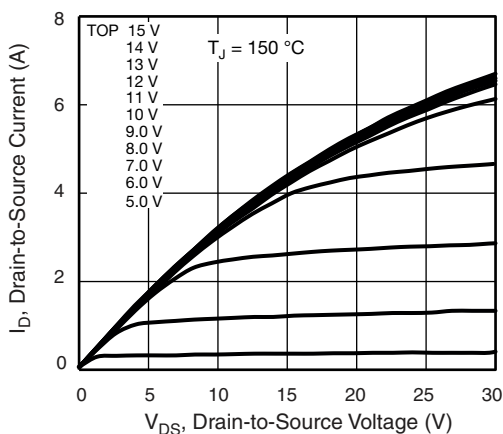
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



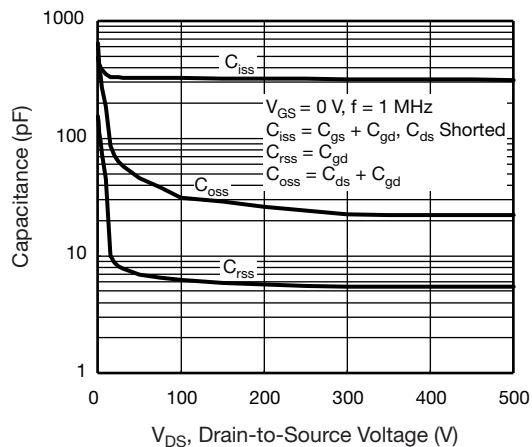
**Fig. 1 - Typical Output Characteristics**



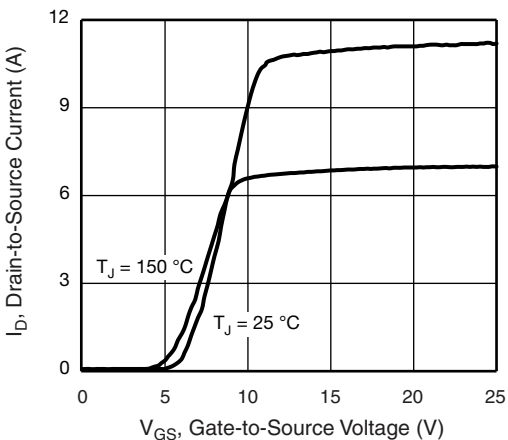
**Fig. 4 - Normalized On-Resistance vs. Temperature**



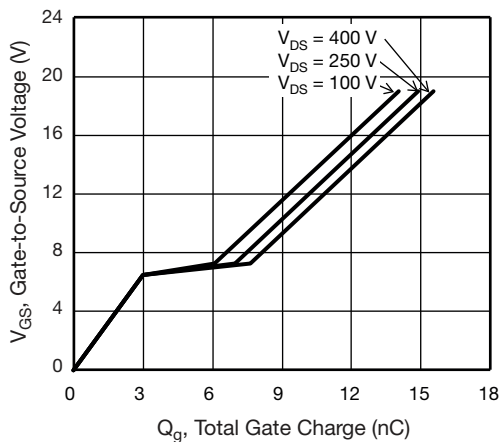
**Fig. 2 - Typical Output Characteristics**



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**



Fig. 7 - Typical Source-Drain Diode Forward Voltage

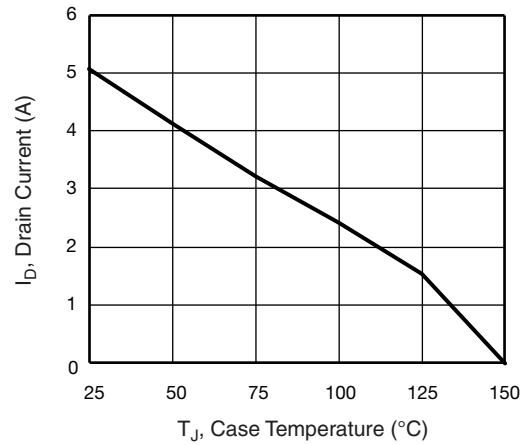


Fig. 9 - Maximum Drain Current vs. Case Temperature



Fig. 8 - Maximum Safe Operating Area

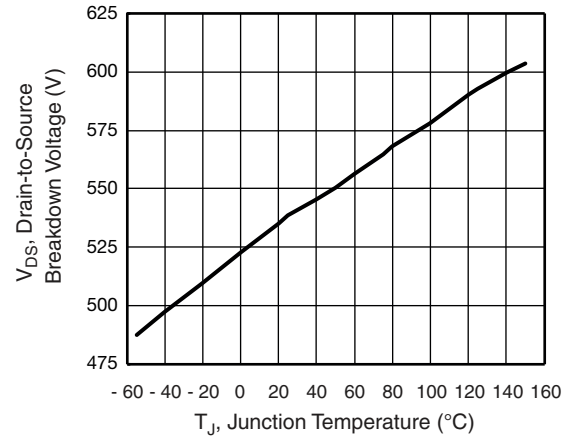


Fig. 10 - Typical Drain-to-Source Voltage vs. Temperature

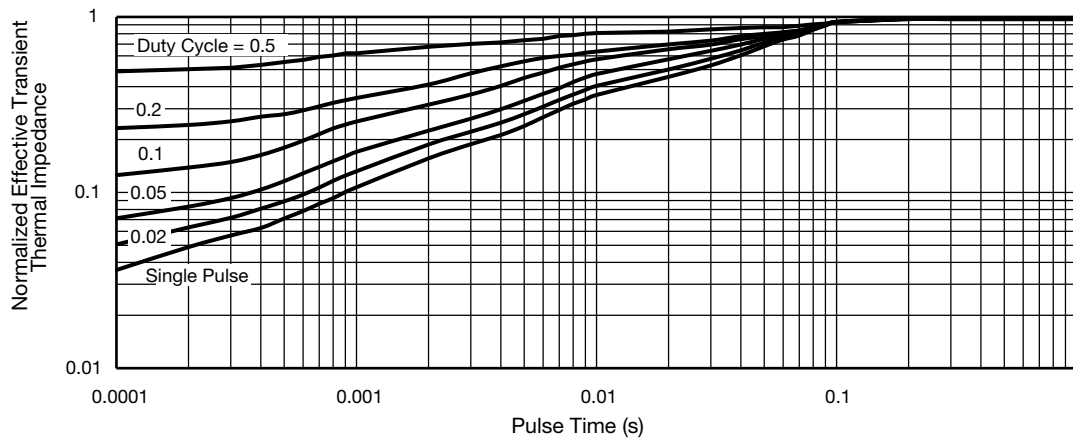


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case



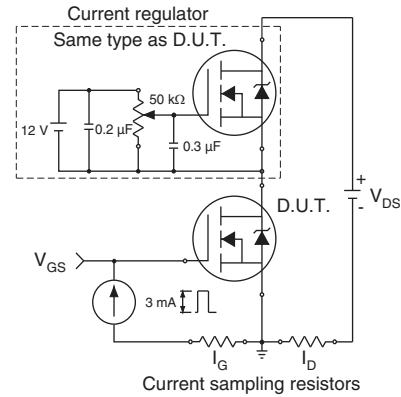
**Fig. 12 - Switching Time Test Circuit**



**Fig. 16 - Basic Gate Charge Waveform**



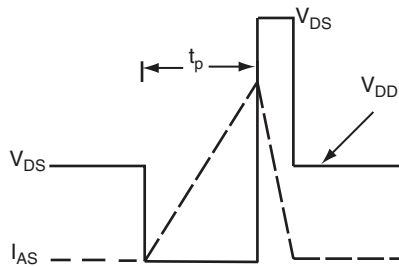
**Fig. 13 - Switching Time Waveforms**



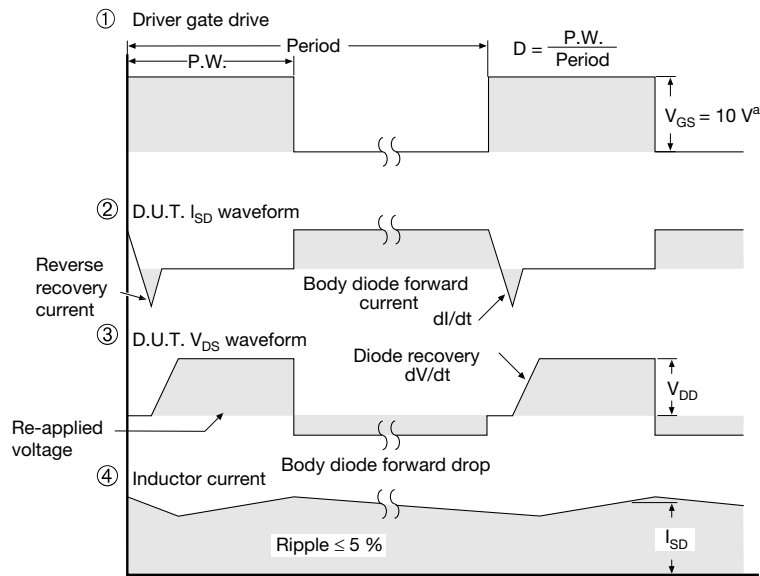
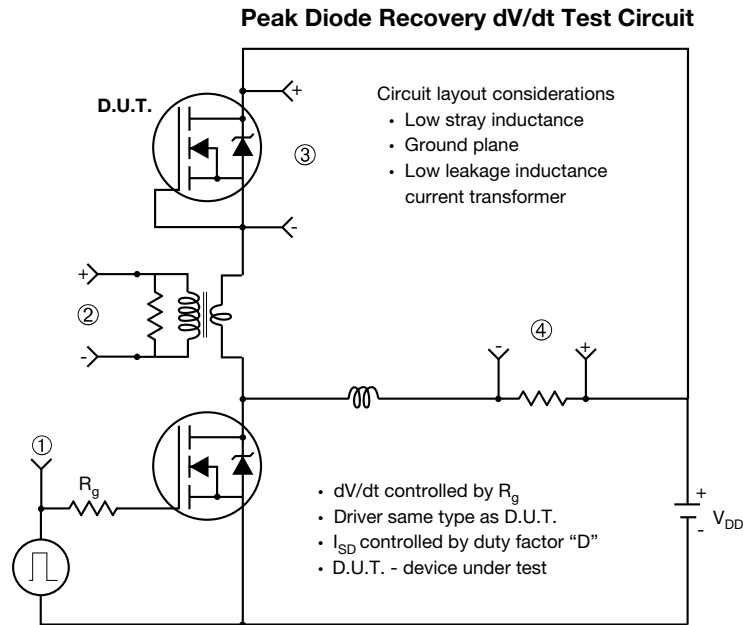
**Fig. 17 - Gate Charge Test Circuit**



**Fig. 14 - Unclamped Inductive Test Circuit**



**Fig. 15 - Unclamped Inductive Waveforms**



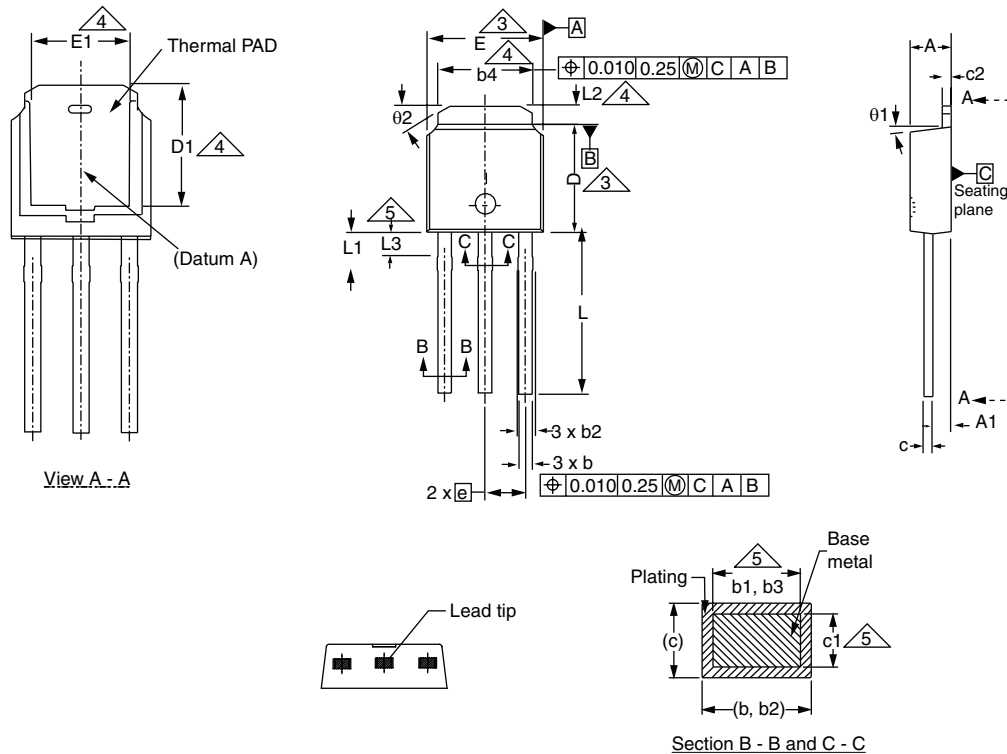
**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 18 - For N-Channel**

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### TO-251AA (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	0.89	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b1	0.65	0.79	0.026	0.031
b2	0.76	1.14	0.030	0.045
b3	0.76	1.04	0.030	0.041
b4	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c1	0.41	0.56	0.016	0.022
c2	0.46	0.86	0.018	0.034
D	5.97	6.22	0.235	0.245

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
e	2.29 BSC		2.29 BSC	
L	8.89	9.65	0.350	0.380
L1	1.91	2.29	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.14	1.52	0.045	0.060
theta1	0'	15'	0'	15'
theta2	25'	35'	25'	35'

ECN: S-82111-Rev. A, 15-Sep-08  
DWG: 5968

#### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension are shown in inches and millimeters.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.13 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions b4, L2, E1 and D1.
5. Lead dimension uncontrolled in L3.
6. Dimension b1, b3 and c1 apply to base metal only.
7. Outline conforms to JEDEC outline TO-251AA.

## RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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